EYP-RWL-1060-00100-0750-SOT01-0000



We focus on power.

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04.01.2010

Version 0.91

RWF/RWI

RIDGE WAVEGUIDE LASER GaAs Semiconductor Laser Diode



General Product Information		
Product	Application	
1060 nm Fabry-Perot Laser with hermetic TO Housing	Spectroscopy	
Monitor Diode		



	Symbol	Unit	min	typ	max
Storage Temperature	Ts	°C	-20		85
Operational Temperature at Case	T _C	°C	-20		50
Forward Current	I _F	mA			180
Reverse Voltage	V _R	V			0
Output Power	P _{opt}	mW			110



Stress in excess of the Absolute Maximum Ratings can cause permanent damage to the device.

Recommended Operational Conditions

	Symbol	Unit	min	typ	max
Operational Temperature at Case	T _c	°C	15		40
Forward Current	I _F	mA			160
Output Power	Popt	mW	10		100

Characteristics at T_{LD} = 25 °C at Begin Of Life

Parameter	Symbol	Unit	min	typ	max
Center Wavelength	λ_{c}	nm	1050	1060	1070
Spectral Width (FWHM)	Δλ	nm			1
Temperature Coefficient of Wavelength	dλ / dT	nm / K		0.3	
Output Power @ I _F = 160 mA	P _{opt}	mW	100		
Slope Efficiency	η_{d}	W / A	0.6	0.8	
Threshold Current	I _{th}	mA			70
Cavity Length	L	μm		750	
Divergence parallel	$\Theta_{ }$	0		10	
Divergence perpendicular	Θ_{\perp}	0		30	

Measurement Conditions / Comments

see imag	es on page 4
total out	put measured with integrating sphere
FWHM	
FWHM	

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eagleyard Photonics GmbH

Rudower Chaussee 29 12490 Berlin GERMANY fon +49. 30. 6392 4520 fax +49. 30. 6392 4529 info@eagleyard.com www.eagleyard.com GLC

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RIDGE WAVEGUIDE LASER

GaAs Semiconductor Laser Diode

°C at E	Begin O	f Life		cont'd
Symbol	Unit	min	typ	max
			TE	
			TEM ₀₀	
		Sin	gle/Multi M	ode
				Symbol Unit min typ TE

RWE/RWL	BAL	DFB/DBR	TPL/TPA

Version 0.91

Measurement Conditions / Comments
E field parallel to Pin 2 - Pin 3 - plane
Fundamental Mode
depending on operating conditions

Monitor Diode

Parameter	Symbol	Unit	min	typ	max
Monitor Detector Responsivity	I _{mon} / P _{opt}	µA / mW	0.5		10
Reverse Voltage Monitor Diode	U _{R MD}	V	3		5

Measurement Conditions / Comments

 $U_R = 5$ V, target values



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RIDGE WAVEGUIDE LASER

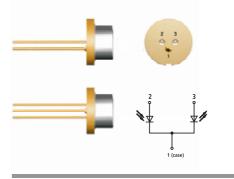
GaAs Semiconductor Laser Diode Fabry-Perot Laser

Symbol	Unit	min	typ	max
d _{EP}	mm	2.30	2.45	2.50
R	mm			0.12
I _{PIN}	mm		14	
	d _{EP} R	d _{ep} mm R mm	d _{EP} mm 2.30 R mm	d _{EP} mm 2.30 2.45 R mm

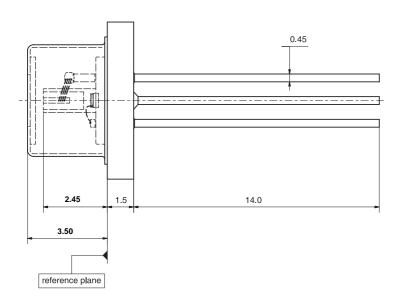
Measurement Conditions / Comments
reference plane: top side of TO header
reference: center of outer diameter of header

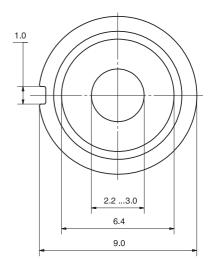
Package Pinout

Ground	1	
Photo Diode (+)	2	
Laser (+)	3	



Package Drawings





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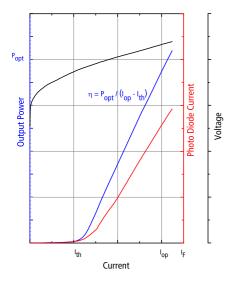
RIDGE WAVEGUIDE LASER GaAs Semiconductor Laser Diode

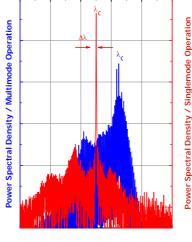


Typical Measurement Results

Output Power vs. Current

Spectra at Specified Optical Output Power





Wavelength

Performance figures, data and any illustrative material provided in this specification are typical and must be specifically confirmed in writing by eagleyard Photonics before they become applicable to any particular order or contract. In accordance with the eagleyard Photonics policy of continuous improvement specifications may change without notice.



800 Village Walk #316 Guilford, CT 06437 Ph: 203-401-8093

Unpacking, Installation and Laser Safety

Unpacking the laser diodes should only be done at electrostatic safe workstations (EPA). Though protection against electro static discharge (ESD) is implemented in the laser package, charges may occur at surfaces. Please store this product in its original package at a dry, clean place until final use. During device installation, ESD protection has to be maintained.

The RWL diode type is known to be sensitive against thermal stress. Operating at moderate temperatures on propper heat sinks will contribute to a long lifetime of the diode.

The laser emission from this diode is close to the invisible infrared region of the electromagnetic spectrum. Avoid direct and/or indirect exposure to the free running beam. Collimating the free running beam with optics as common in optical instruments will increase threat to the human eye.

Each laser diode will come with an individual test protocol verifying the parameters given in this document.







GLC



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